CSD25310Q2 20 V P-Channel NexFET™ Power MOSFETs

1 Features

- Ultra-Low Q_g and Q_{gd}
- Low On Resistance
- Low Thermal Resistance
- Pb-Free
- RoHS Compliant
- Halogen Free
- SON 2-mm × 2-mm Plastic Package

2 Applications

- Battery Management
- Load Management
- Battery Protection

3 Description

This 19.9 mΩ, –20 V P-Channel device is designed to deliver the lowest on resistance and gate charge in the smallest outline possible with excellent thermal characteristics in an ultra-low profile. Its low on resistance coupled with an extremely small footprint in a SON 2 mm × 2 mm plastic package make the device ideal for battery operated space constrained operations.

Product Summary

T_A = 25°C		TYPICAL VALUE		UNIT
V_{DS}	Drain-to-Source Voltage	–20		V
Q_g	Gate Charge Total (–4.5 V)	3.6		nC
Q_{gd}	Gate Charge Gate to Drain	0.5		nC
$R_{DS(on)}$	Drain-to-Source On Resistance	V_{GS} = –1.8 V	59.0	mΩ
		V_{GS} = –2.5 V	27.0	mΩ
		V_{GS} = –4.5 V	19.9	mΩ
$V_{GS(th)}$	Threshold Voltage	-0.85		V

Ordering Information(1)

Device	Media	Qty	Package	Ship
CSD25310Q2	7-Inch Reel	3000	SON 2 x 2 mm Plastic Package	Tape and Reel
CSD25310Q2T	7-Inch Reel	250		

(1) For all available packages, see the orderable addendum at the end of the data sheet.

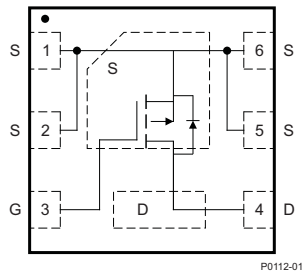
Absolute Maximum Ratings

T_A = 25°C		VALUE	UNIT
V_{DS}	Drain-to-Source Voltage	–20	V
V_{GS}	Gate-to-Source Voltage	±8	V
I_D	Continuous Drain Current (Package Limit)	–20	A
	Continuous Drain Current(1)	–9.6	A
I_{DM}	Pulsed Drain Current(2)	48	A
P_D	Power Dissipation(1)	2.9	W
T_J, T_{stg}	Operating Junction and Storage Temperature Range	–55 to 150	°C

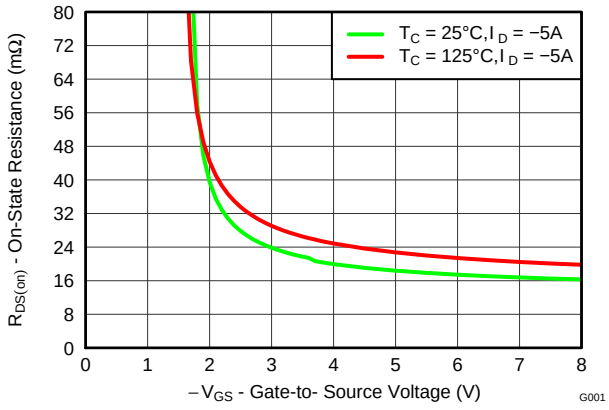
(1) $R_{\theta JA}$ = 43°C/W on 1 in² Cu (2 oz.) on .060-inch thick FR4 PCB.

(2) Pulse duration 10 µs, duty cycle ≤2%

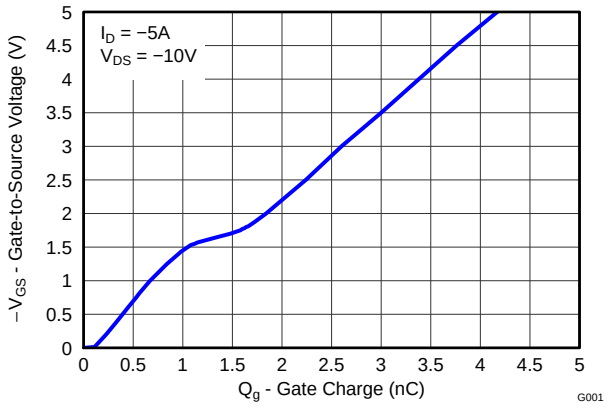
Top View



$R_{DS(on)}$ vs V_{GS}



Gate Charge



An IMPORTANT NOTICE at the end of this data sheet addresses availability, warranty, changes, use in safety-critical applications, intellectual property matters and other important disclaimers. PRODUCTION DATA.

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4 Revision History

Changes from Original (January 2014) to Revision A **Page**

- Revised "Pb-Free Terminal Plating" to Only State "Pb-Free" ... 1
- Added small reel option to the Ordering Information Table ... 1

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5 Specifications

5.1 Electrical Characteristics

T_A = 25°C, unless otherwise specified

PARAMETER		TEST CONDITIONS	MIN	TYP	MAX	UNIT
STATIC CHARACTERISTICS						
BV_{DSS}	Drain-to-Source Voltage	V_{GS} = 0 V, I_D = –250 µA	–20			V
I_{DSS}	Drain-to-Source Leakage Current	V_{GS} = 0 V, V_{DS} = –16 V			–1	µA
I_{GSS}	Gate-to-Source Leakage Current	V_{DS} = 0 V, V_{GS} = –8 V			–100	nA
$V_{GS(th)}$	Gate-to-Source Threshold Voltage	V_{DS} = V_{GS}, I_{DS} = –250 µA	–0.55	–0.85	–1.10	V
$R_{DS(on)}$	Drain-to-Source On Resistance	V_{GS} = –1.8 V, I_{DS} = –5 A		59.0	89.0	mΩ
		V_{GS} = –2.5 V, I_{DS} = –5 A		27.0	32.5	mΩ
		V_{GS} = –4.5 V, I_{DS} = –5 A		19.9	23.9	mΩ
g_{fs}	Transconductance	V_{DS} = –16 V, I_{DS} = –5 A		34		S
DYNAMIC CHARACTERISTICS						
C_{ISS}	Input Capacitance	V_{GS} = 0 V, V_{DS} = –10 V, f = 1 MHz		504	655	pF
C_{OSS}	Output Capacitance			281	365	pF
C_{RSS}	Reverse Transfer Capacitance			16.7	21.7	pF
R_g	Series Gate Resistance			1.9		Ω
Q_g	Gate Charge Total (–4.5 V)	V_{DS} = –10 V, I_{DS} = –5 A		3.6	4.7	nC
Q_{gd}	Gate Charge Gate to Drain			0.5		nC
Q_{gs}	Gate Charge Gate to Source			1.1		nC
$Q_{g(th)}$	Gate Charge at V_{th}			0.6		nC
Q_{OSS}	Output Charge	V_{DS} = –10 V, V_{GS} = 0 V		5.0		nC
$t_{d(on)}$	Turn On Delay Time	V_{DS} = –10 V, V_{GS} = –4.5 V, I_{DS} = –5 A, R_G = 2 Ω		8		ns
t_r	Rise Time			15		ns
$t_{d(off)}$	Turn Off Delay Time			15		ns
t_f	Fall Time			5		ns
DIODE CHARACTERISTICS						
V_{SD}	Diode Forward Voltage	I_{DS} = –5 A, V_{GS} = 0 V		–0.8	–1.0	V
Q_{rr}	Reverse Recovery Charge	V_{DD} = –10 V, I_F = –5 A, di/dt = 200 A/µs		9.2		nC
t_{rr}	Reverse Recovery Time			13		ns

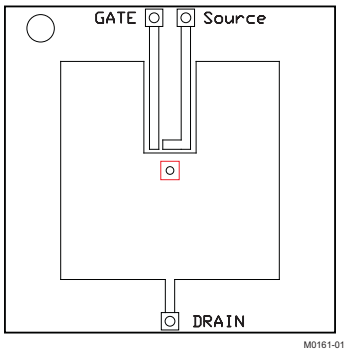
5.2 Thermal Information

(T_A = 25°C unless otherwise stated)

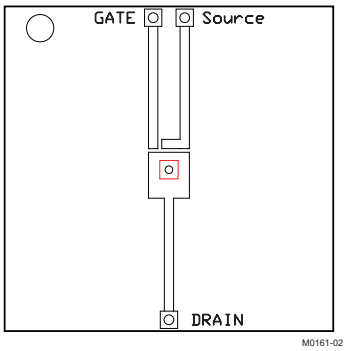
THERMAL METRIC		MIN	TYP	MAX	UNIT
$R_{\theta JC}$	Thermal Resistance Junction to Case(1)			4.5	°C/W
$R_{\theta JA}$	Thermal Resistance Junction to Ambient(1)(2)			55	

(1) $R_{\theta JC}$ is determined with the device mounted on a 1-inch^2 (6.45-cm^2), 2-oz. (0.071-mm thick) Cu pad on a 1.5-inch × 1.5-inch (3.81-cm × 3.81-cm), 0.06-inch (1.52-mm) thick FR4 PCB. $R_{\theta JC}$ is specified by design, whereas $R_{\theta JA}$ is determined by the user's board design.
(2) Device mounted on FR4 material with 1-inch^2 (6.45-cm^2), 2-oz. (0.071-mm thick) Cu.

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Max $R_{\theta JA}$ = 55 when mounted on 1 inch^2 (6.45 cm^2) of 2-oz. (0.071-mm thick) Cu.



Max $R_{\theta JA}$ = 215 when mounted on minimum pad area of 2-oz. (0.071-mm thick) Cu.

5.3 Typical MOSFET Characteristics

(T_A = 25°C unless otherwise stated)

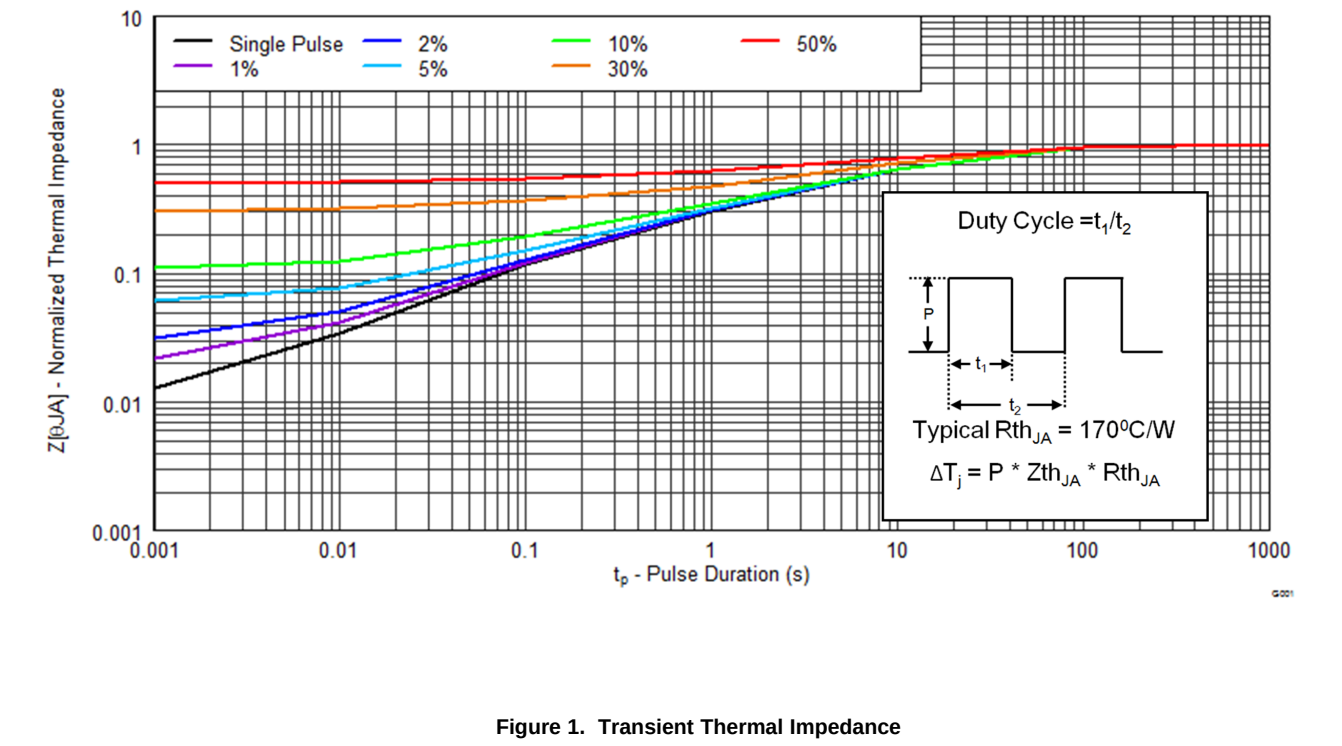


Figure 1. Transient Thermal Impedance

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Typical MOSFET Characteristics (continued)

(T_A = 25°C unless otherwise stated)

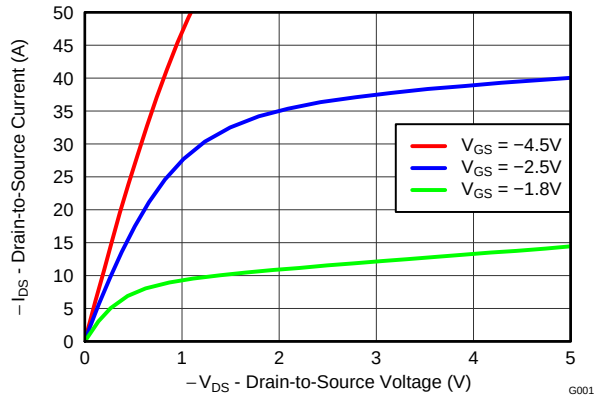


Figure 2. Saturation Characteristics

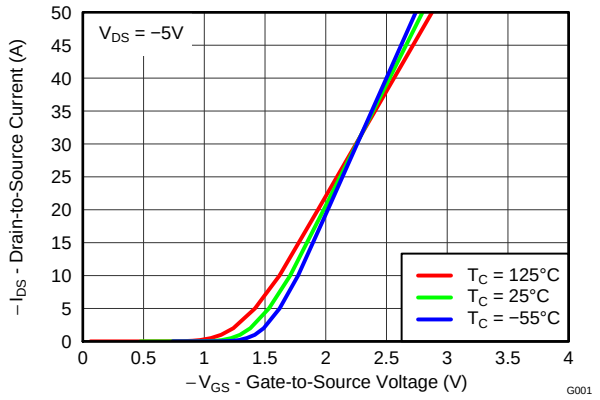


Figure 3. Transfer Characteristics

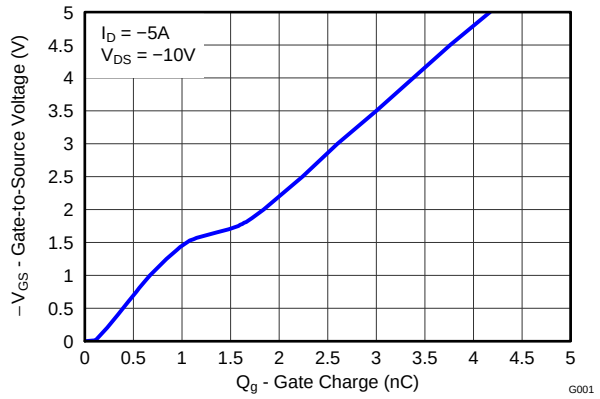


Figure 4. Gate Charge

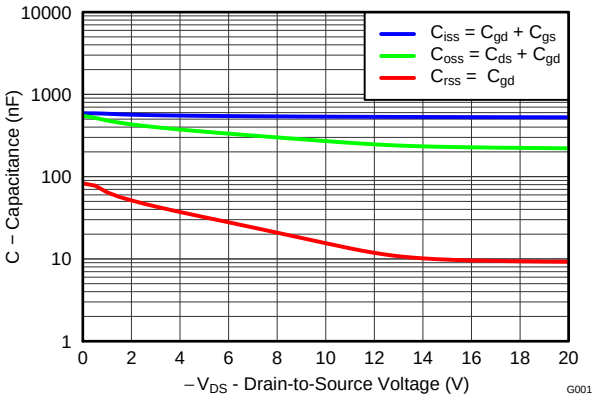


Figure 5. Capacitance

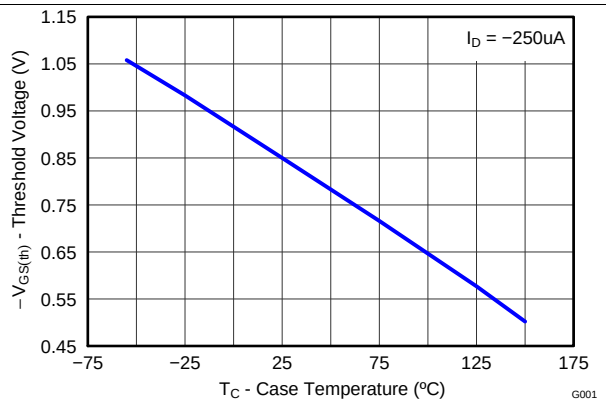


Figure 6. Threshold Voltage vs Temperature

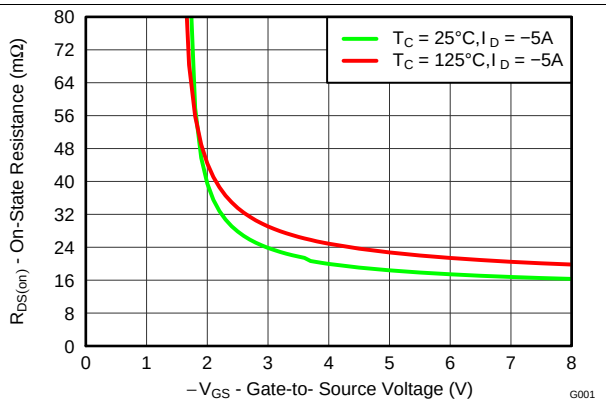


Figure 7. On-State Resistance vs Gate-to-Source Voltage

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Typical MOSFET Characteristics (continued)

(T_A = 25°C unless otherwise stated)

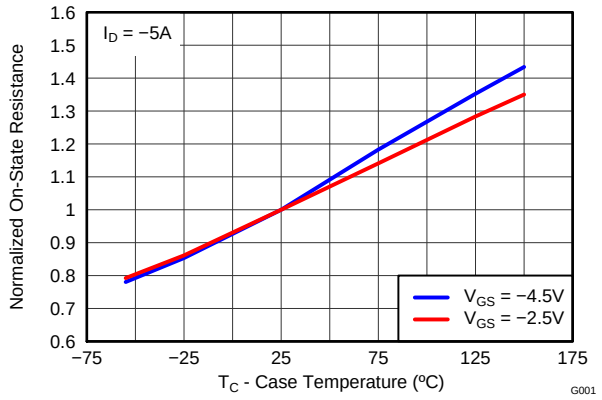


Figure 8. Normalized On-State Resistance vs Temperature

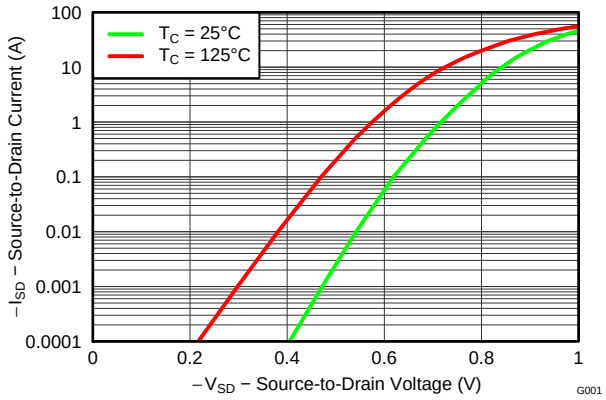


Figure 9. Typical Diode Forward Voltage

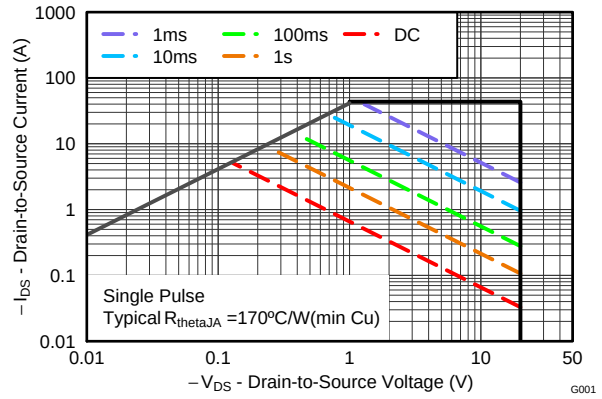


Figure 10. Maximum Safe Operating Area

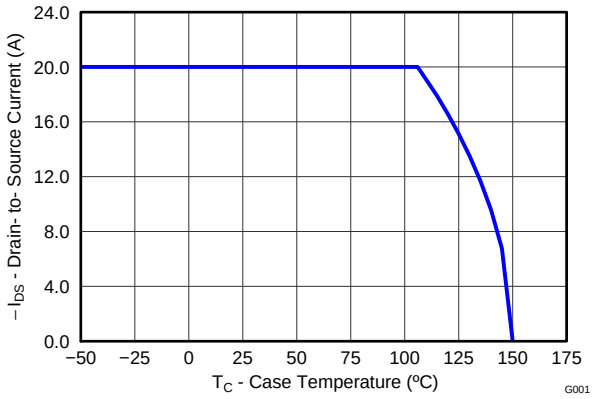


Figure 11. Maximum Drain Current vs Temperature

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6 Device and Documentation Support

6.1 Trademarks

NexFET is a trademark of Texas Instruments.
All other trademarks are the property of their respective owners.

6.2 Electrostatic Discharge Caution



These devices have limited built-in ESD protection. The leads should be shorted together or the device placed in conductive foam during storage or handling to prevent electrostatic damage to the MOS gates.

6.3 Glossary

SLYZ022 — *TI Glossary*.

This glossary lists and explains terms, acronyms and definitions.

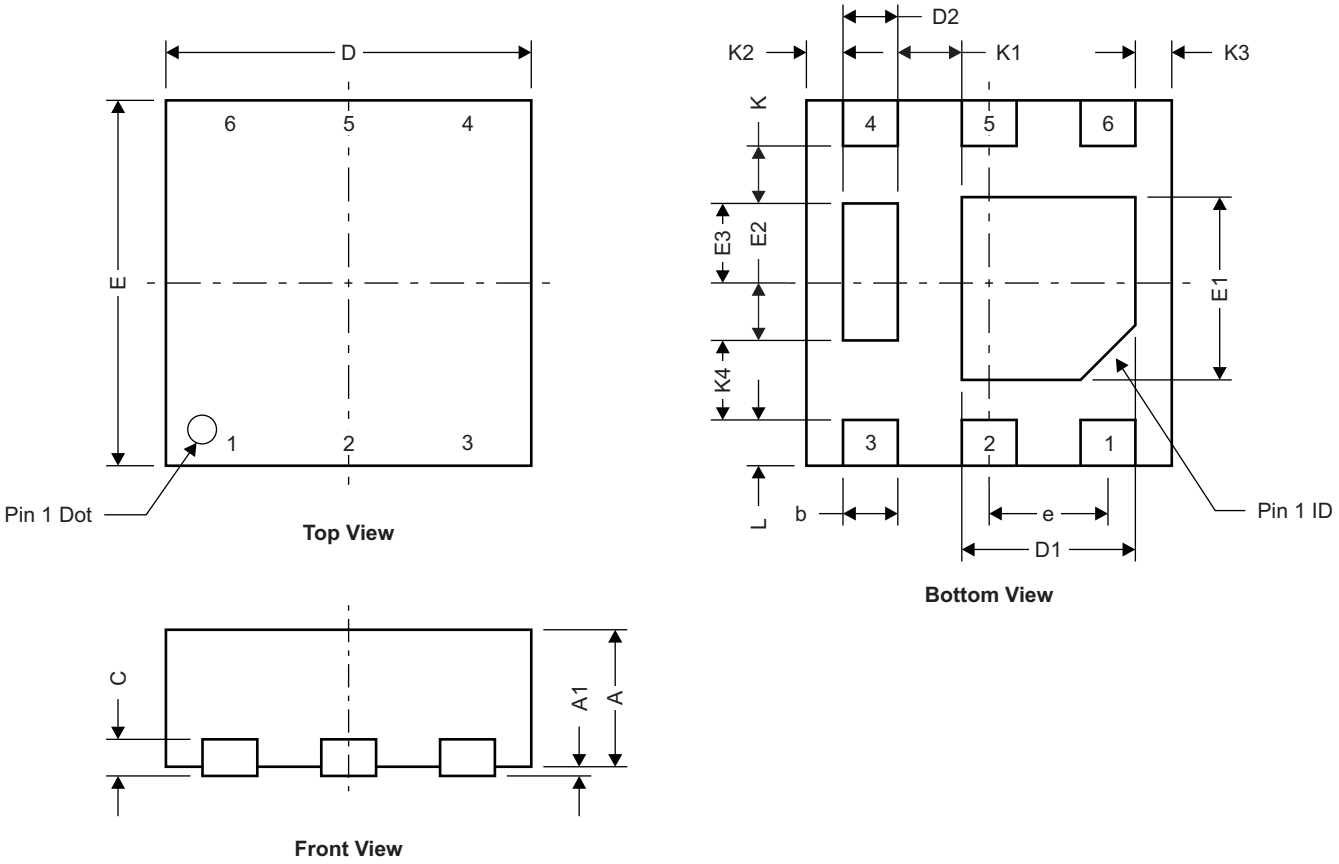
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7 Mechanical, Packaging, and Orderable Information

The following pages include mechanical packaging and orderable information. This information is the most current data available for the designated devices. This data is subject to change without notice and revision of this document. For browser-based versions of this data sheet, refer to the left-hand navigation.

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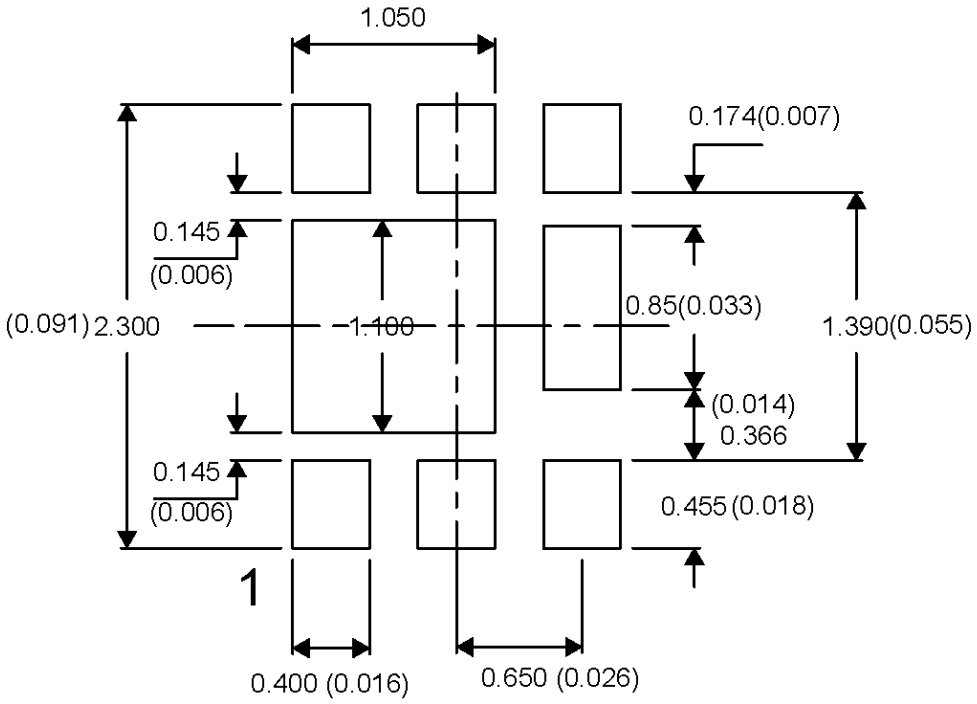
7.1 Q2 Package Dimensions



DIM	MILLIMETERS			INCHES		
	MIN	NOM	MAX	MIN	NOM	MAX
A	0.700	0.750	0.800	0.028	0.030	0.032
A1	0.000		0.050	0.000		0.002
b	0.250	0.300	0.350	0.010	0.012	0.014
C	0.203 TYP			0.008 TYP		
D	2.000 TYP			0.080 TYP		
D1	0.900	0.950	1.000	0.036	0.038	0.040
D2	0.300 TYP			0.012 TYP		
E	2.000 TYP			0.080 TYP		
E1	0.900	1.000	1.100	0.036	0.040	0.044
E2	0.280 TYP			0.0112 TYP		
E3	0.470 TYP			0.0188 TYP		
e	0.650 TYP			0.026 TYP		
K	0.280 TYP			0.0112 TYP		
K1	0.350 TYP			0.014 TYP		
K2	0.200 TYP			0.008 TYP		
K3	0.200 TYP			0.008 TYP		
K4	0.470 TYP			0.0188 TYP		
L	0.200	0.25	0.300	0.008	0.010	0.012

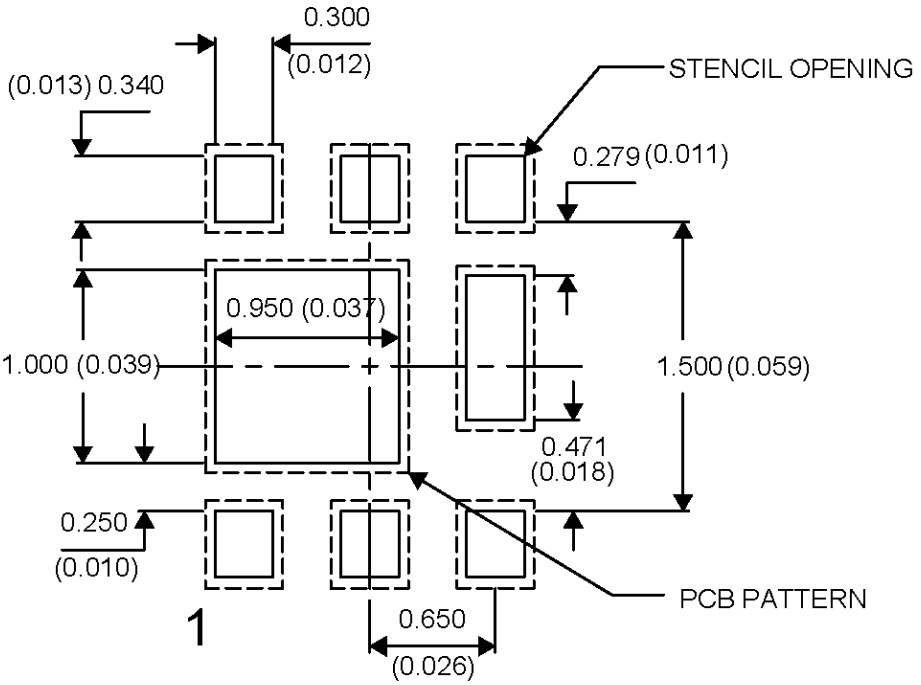
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7.2 Recommended PCB Pattern



For recommended circuit layout for PCB designs, see application note SLPA005 – *Reducing Ringing Through PCB Layout Techniques*.

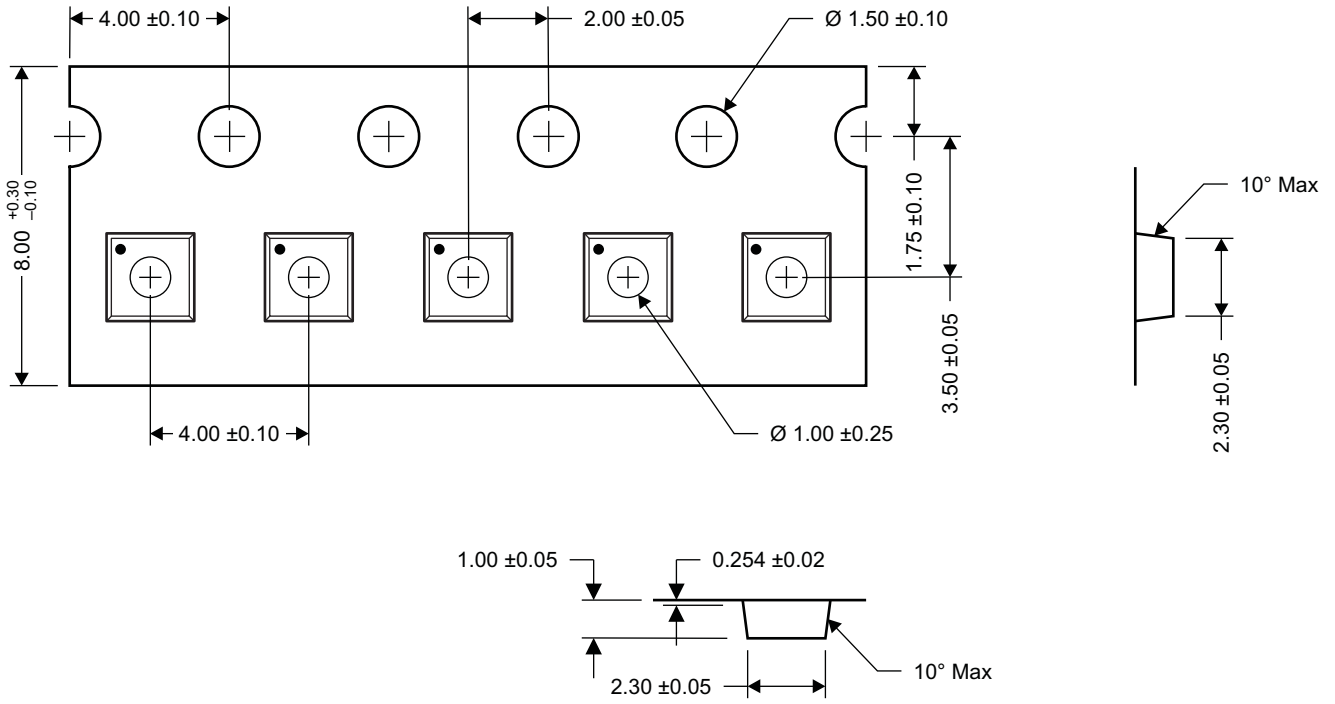
7.3 Recommended Stencil Pattern



Note: All dimensions are in mm, unless otherwise specified.

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7.4 Q2 Tape and Reel Information



Notes: 1. Measured from centerline of sprocket hole to centerline of pocket
2. Cumulative tolerance of 10 sprocket holes is ±0.20
3. Other material available
4. Typical SR of form tape Max 10^9 OHM/SQ
5. All dimensions are in mm, unless otherwise specified.

PACKAGING INFORMATION

Orderable Device	Status (1)	Package Type	Package Drawing	Pins	Package Qty	Eco Plan (2)	Lead/Ball Finish (6)	MSL Peak Temp (3)	Op Temp (°C)	Device Marking (4/5)	Samples
CSD25310Q2	ACTIVE	WSON	DQK	6	3000	Green (RoHS & no Sb/Br)	NIPDAU | SN	Level-1-260C-UNLIM	-55 to 150	2530	Samples
CSD25310Q2T	ACTIVE	WSON	DQK	6	250	Green (RoHS & no Sb/Br)	SN	Level-1-260C-UNLIM	-55 to 150	2530	Samples

(1) The marketing status values are defined as follows:
ACTIVE: Product device recommended for new designs.
LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.
NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.
PREVIEW: Device has been announced but is not in production. Samples may or may not be available.
OBSOLETE: TI has discontinued the production of the device.

(2) **RoHS:** TI defines "RoHS" to mean semiconductor products that are compliant with the current EU RoHS requirements for all 10 RoHS substances, including the requirement that RoHS substance do not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, "RoHS" products are suitable for use in specified lead-free processes. TI may reference these types of products as "Pb-Free".
RoHS Exempt: TI defines "RoHS Exempt" to mean products that contain lead but are compliant with EU RoHS pursuant to a specific EU RoHS exemption.
Green: TI defines "Green" to mean the content of Chlorine (Cl) and Bromine (Br) based flame retardants meet JS709B low halogen requirements of <=1000ppm threshold. Antimony trioxide based flame retardants must also meet the <=1000ppm threshold requirement.

(3) MSL, Peak Temp. - The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.

(4) There may be additional marking, which relates to the logo, the lot trace code information, or the environmental category on the device.

(5) Multiple Device Markings will be inside parentheses. Only one Device Marking contained in parentheses and separated by a "~" will appear on a device. If a line is indented then it is a continuation of the previous line and the two combined represent the entire Device Marking for that device.

(6) Lead/Ball Finish - Orderable Devices may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead/Ball Finish values may wrap to two lines if the finish value exceeds the maximum column width.

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